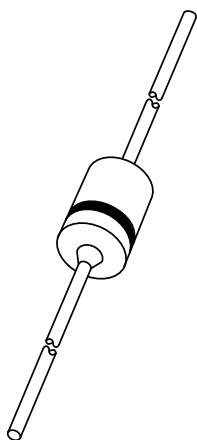


# **DATA SHEET**



## **1N4148; 1N4446; 1N4448** **High-speed diodes**

Product specification

1996 Sep 03

Supersedes data of April 1996

File under Discrete Semiconductors, SC01

## Diodes rapides

**1N4148; 1N4446; 1N4448**

### Caracteristiques

- Encapsulees hermetiquement dans un boitier SOD27 (DO-35)
- Commutation rapide : max. 4 ns
- Application generale
- Tension continue inverse : max. 75 V
- Tension de pointe repetitive inverse: max. 75 V
- Courant direct de pointe repetitif : max. 450 mA.

### DESCRIPTION

Les 1N4148, 1N4446, 1N4448 sont des diodes de commutations rapides utilisant le technologie planar, encapsulees hermetiquement dans un boitier de verre SOD27 (DO-35) .

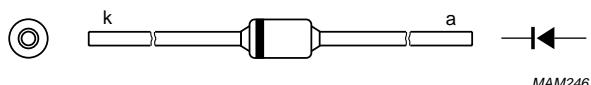


Fig.1 Boitier simplifie (SOD27; DO-35) et symbole.

### APPLICATIONS

- Commutation rapide.

### Valeurs limites

En accord avec les valeurs maximums absolues du systeme (IEC 134).

Symbol	Parametre	Conditions	MIN.	MAX.	UNITE
$V_{RRM}$	Tension de pointe repetitive inverse		—	75	V
$V_R$	Tension continue inverse		—	75	V
$I_F$	Courant direct continu	voir Fig.2; note 1	—	200	mA
$I_{FRM}$	Courant direct de pointe repetitif		—	450	mA
$I_{FSM}$	Courant direct de pointe non repetitif	Onde carree ; $T_j = 25^\circ\text{C}$  $t = 1 \mu\text{s}$ $t = 1 \text{ ms}$ $t = 1 \text{ s}$	— — —	4 1 0.5	A
$P_{tot}$	Puissance totale dissipée	$T_{amb} = 25^\circ\text{C}$ ; note 1	—	500	mW
$T_{stg}$	Temperature de stockage		-65	+200	°C
$T_j$	Temperature de jonction		—	200	°C

### Note

1.Composant monte sur un circuit imprime avec des longueurs de broches de 10mm

## Diodes rapides

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**CARACTERISTIQUES ELECTRIQUES** $T_j = 25^\circ\text{C}$ ; sauf information contraire.

<b>Symbol</b>	<b>Parametre</b>	<b>Conditions</b>	<b>MIN.</b>	<b>MAX.</b>	<b>UNITE</b>
$V_F$	Tension directe 1N4148 1N4446 1N4448	$I_F = 10 \text{ mA}$	—	1.0	V
		$I_F = 20 \text{ mA}$	—	1.0	V
		$I_F = 5 \text{ mA}$	0.62	0.72	V
		$I_F = 100 \text{ mA}$	—	1.0	V
$I_R$	Courant inverse	$V_R = 20 \text{ V}$	25	nA	
		$V_R = 20 \text{ V}; T_j = 150^\circ\text{C}$	—	50	$\mu\text{A}$
$I_R$	Courant inverse ; 1N4448	$V_R = 20 \text{ V}; T_j = 100^\circ\text{C}$	—	3	$\mu\text{A}$
$C_d$	Capacite de la diode	$f = 1 \text{ MHz}; V_R = 0$	—	4	pF
$t_{rr}$	Temps de recouvrement inverse	Avec commutation : $I_F = 10 \text{ mA}$ à $I_R = 60 \text{ mA}; R_L = 100 \Omega$ ; mesure à $I_R = 1 \text{ mA}$	—	4	ns
$V_{fr}$	Tension de recouvrement directe	Avec commutation $I_F = 50 \text{ mA}$ ; $t_r = 20 \text{ ns}$	—	2.5	V

**CARACTERISTIQUES THERMIQUE**

<b>Symbol</b>	<b>Parametre</b>	<b>Conditions</b>	<b>Valeur</b>	<b>Unite</b>
$R_{th j-tp}$	Resistance thermique jonction boitier	longueur des broches 10 mm	240	K/W
$R_{th j-a}$	Resistance thermique jonction air ambiant	longueur des broches 10 mm ; note 1	350	K/W

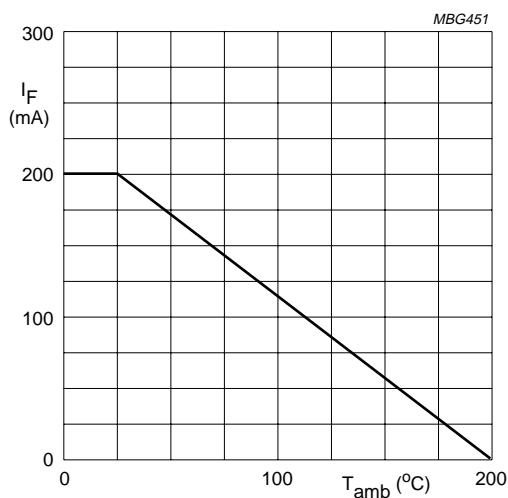
**Note**

1.Composant monte sur circuit imprimé sans trou métallisé

## Diodes Rapides

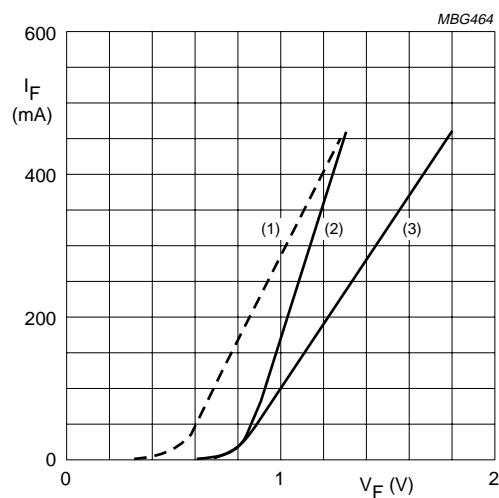
1N4148; 1N4446; 1N4448

## GRAPHICAL DATA



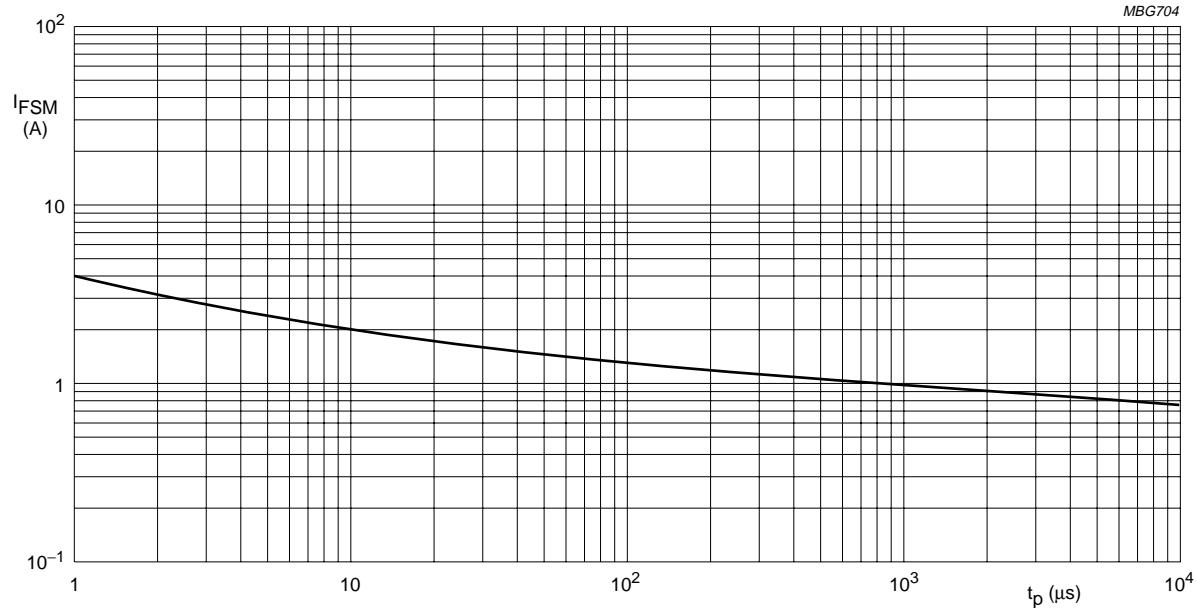
Device mounted on an FR4 printed-circuit board; lead length 10 mm.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1)  $T_j = 175$  °C; typical values.
- (2)  $T_j = 25$  °C; typical values.
- (3)  $T_j = 25$  °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



Based on square wave currents.

$T_j = 25$  °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

## High-speed diodes

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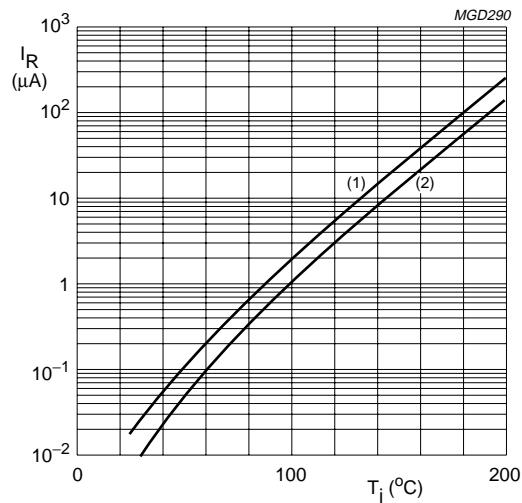


Fig.5 Reverse current as a function of junction temperature.

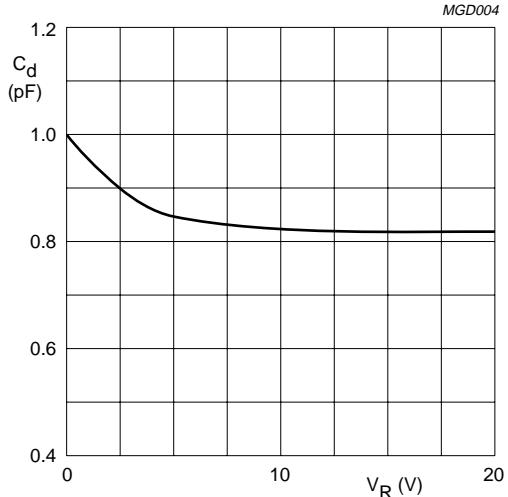


Fig.6 Diode capacitance as a function of reverse voltage; typical values.

## High-speed diodes

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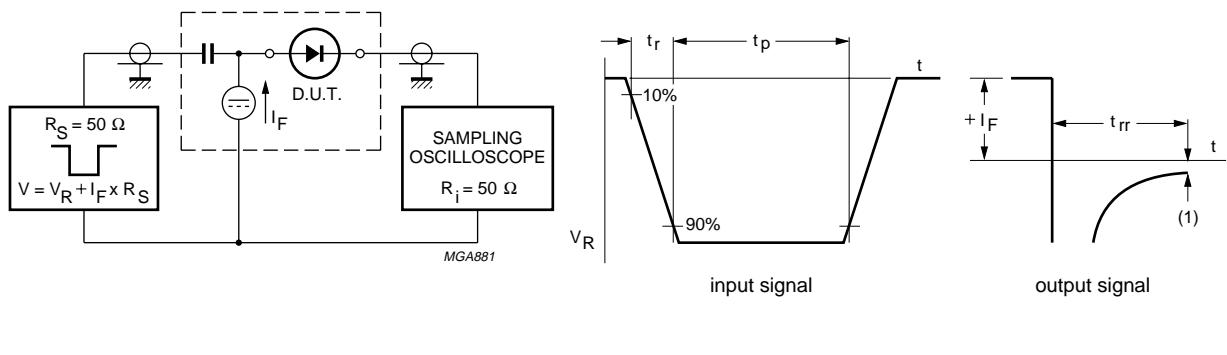
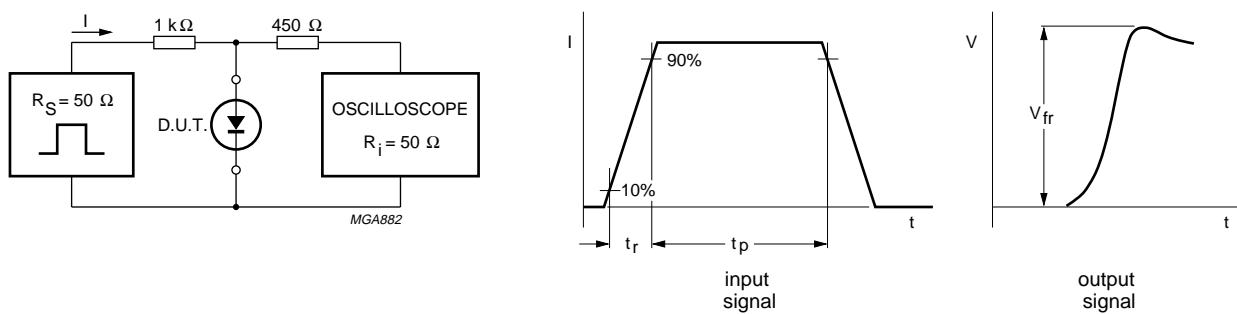


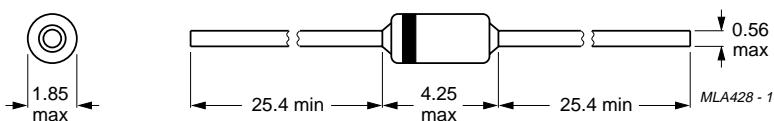
Fig.7 Reverse recovery voltage test circuit and waveforms.



## High-speed diodes

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## PACKAGE OUTLINE



Dimensions in mm.

Fig.9 SOD27 (DO-35).

## DEFINITIONS

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

## LIFE SUPPORT APPLICATIONS

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